

Attorney's Docket No. 5308-156

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Ryu et al.  
Serial No.: 09/911,995  
Filed: July 24, 2001  
For: SILICON CARBIDE POWER METAL-OXIDE SEMICONDUCTOR FIELD  
EFFECT TRANSISTORS HAVING A SHORTING CHANNEL AND METHODS  
OF FABRICATING SILICON CARBIDE METAL-OXIDE SEMICONDUCTOR  
FIELD EFFECT TRANSISTORS HAVING A SHORTING CHANNEL

Group Art Unit: 2811

Confirmation No.: 5240

Examiner: Gene Munson

Date: December 23, 2003

Mail Stop Fee Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SUPPLEMENTAL  
INFORMATION DISCLOSURE STATEMENT**

Sir:

Attached is a list of documents on form PTO-1449 together with a copy of each identified document. It is requested that these documents be considered by the Examiner and officially made of record in accordance with the provisions of 37 C.F.R. § 1.56 and Section 609 of the MPEP.

This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action.

The Commissioner is authorized to charge the \$180.00 fee specified in 37 C.F.R. § 1.17(p). This amount is believed to be correct. However, the Commissioner is authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50-0220.

Respectfully submitted,

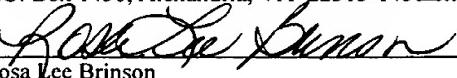
  
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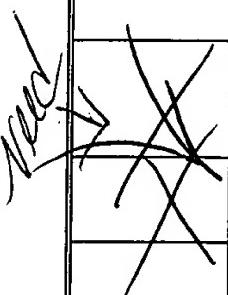
**Certificate of Mailing under 37 CFR 1.8 (or 1.10)**  
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Mail Stop Fee Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on December 23, 2003.

  
Rosa Lee Brinson

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office				Attorney Docket Number 5308-156			Serial No. 09/911,995
<p style="text-align: center;">LIST OF DOCUMENTS CITED BY APPLICANT</p> <p>(use several sheets if necessary)</p> <p><i>O I P E</i> DEC 29 2003 PATENT &amp; TRADEMARK OFFICE</p>				Applicants: Ryu et al.			
				Filing Date: July 24, 2001			Group: 2811
				U. S. PATENT DOCUMENTS			
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	1.	5,587,870	12/24/96	Anderson et al.	361	313	
	2.	5,877,045	3/2/99	Kapoor	438	151	
	3.	6,136,728	10/24/00	Wang	438	773	
	4.	6,063,698	05/16/00	Tseng et al.	438	585	
	5.	6,048,766	04/11/00	Gardner et al.	438	257	
	6.	6,028,012	02/22/00	Wang	438	779	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
	7.	WO99/63591	12/09/99	PCT			
	8.	WO00/13236	03/09/00	PCT			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
	9.	Mutin, P. Herbert, "Control of the Composition and Structure of Silicon Oxycarbide and Oxynitride Glasses Derived from Polysiloxane Precursors," <i>Journal of Sol-Gel Science and Technology</i> . Vol. 14 (1999) pp. 27-38.					
	10.	del Prado et al. "Full Composition Range Silicon Oxynitride Films Deposited by ECR-PECVD at Room Temperatures," <i>Thin Solid Films</i> . Vol. 343-344 (1999) p. 437-440.					
	11.	Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," <i>IEEE Transactions on Electron Devices</i> . Vol. 47, No. 2, February 2000.					

EXAMINER  
EXAMINER

DATE CONSIDERED  
 Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>FORM PTO-1449 U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>				Attorney Docket Number 5308-156			Serial No. 09/911,995
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